

B1
cont'd.
a silicon layer formed over the buried oxide layer, wherein an origin of a doping profile of the silicon layer is within a body region of the device and has a dopant level of approximately zero.

B2
8. (Amended) A high frequency semiconductor device having a shifted doping profile, comprising:

a buried oxide layer formed over a semiconductor substrate;

a silicon layer formed over the buried oxide layer, wherein the silicon layer comprises a source region, a body region, a drift region, and a drain region; and

a top oxide layer formed over the silicon layer, wherein a doping profile of the silicon layer has an origin that has a dopant level of approximately zero, and wherein the origin is within the body region, approximately 2 to 4 μ m from an edge of the top oxide layer.

Remarks

Claims 1-13 are pending. By this Amendment, claims 1 and 8 have been amended.

Reconsideration and allowance are respectfully requested in view of the above amendments and the following remarks.

Claims 1-13 are rejected under 35 U.S.C. §103(a) as being unpatentable over Simpson et al. (US 6,232,636), hereafter "Simpson." Claims 1-13 are also rejected under 35 U.S.C. §103(a) as being unpatentable over Merchant (US 5,246,870), hereafter "Merchant '870," or Letavic et al. (US 5,969,387), hereafter "Letavic," or Merchant et al. (US 5,300,448), hereafter "Merchant